Number	Hits	Search Text	DB	Time stamp
1	1384	phase near3 chang\$3 near3 device	USPAT;	2003/10/31 06:3
_	150.	phase hears changes hears active	US-PGPUB	1
2	564	(phase near3 chang\$3 near3 device) and (gate	USPAT;	2003/10/31 06:3
	001	electrode)	US - PGPUB	i
ı İ	174	((phase near3 chang\$3 near3 device) and	USPAT;	2003/10/31 06:2
		(gate electrode)) and etch\$3	US-PGPUB	2003, 20, 01
4	732	phase near3 chang\$3 near3 device	EPO; JPO;	1 2003/10/31 06:3
1	.52	phase hears changes hears active	DERWENT;	, 2003, 20, 31 03.2
			IBM TDB	1
5	5.3	(phase near3 chang\$3 near3 device) and (gate	EPO; JPO;	2003/10/31 06:3
	33	electrode)	DERWENT;	1
		CICCIIOMC)	IBM TDB	1
_	2202	tapered near5 electrode	USPĀT;	2003/10/31 06:2
	2202	capered nears erections	US-PGPUB	2003, 20, 32 00.2
-	112	(tapered near5 electrode) and trench	USPAT;	2003/10/30 12:0
	112	(capered hears electrode, and trench	US - PGPUB	2003/10/30 12.0
_	1182	tapered near5 electrode	EPO; JPO;	2003/10/30 12:0
	1102	capered hears electrode		2003/10/30 12:0
			DERWENT;	i
	0	/b	IBM_TDB	2002/20/20 10 /
- i	0	(tapered near5 electrode) and trench	USPAT;	2003/10/30 12:0
			US-PGPUB	1 0000 (45 (
	0	(tapered near5 electrode) and (trench onen\$3	USPAT;	2003/10/30 12:0
		recess hole via contact)	US - PGPUB	1
i i	2000		USPAT;	2003/10/30 15:3
Ť		recess hole via contact)	US-PGPUB	
-	1645	tapered near5 electrode	US-PGPUB;	2003/10/30 15::
			EPO; JPO;	!
			DERWENT;	
			IBM TDB	1
-	410	(tapered near5 electrode) and (trench onen\$3	EPO; JPO;	2003/10/30 15:3
		recess hole via contact)	DERWENT;	1
		100000 11010 110 001100007	IBM TDB	
. i	77	((tapered near5 electrode) and (trench	EPO; JPO;	2003/10/30 15:
†	, ,	onen\$3 recess hole via contact)) and	DERWENT;	2003/10/30 13:
		(semiconductor wafer)	IBM TDB	
1	2931			2002/10/20 15:
į	293I	tapered near5 (electrode gate)	USPAT;	2003/10/30 15:3
i	2540	(US-PGPUB	0000/10/00 15
	2649	(tapered near5 (electrode gate)) and (trench	USPAT;	2003/10/30 15:
1	1207	onen\$3 recess hole via contact)	US-PGPUB	0000 (30 (00 05)
-	1307		USPAT;	2003/10/30 15:
į		(trench onen\$3 recess hole via contact)) and	US-PGPUB	i
ĺ		(semiconductor wafer substrate)	!	1
	984	(((tapered near5 (electrode gate)) and	USPAT;	2003/10/30 15:
		(trench onen\$3 recess hole via contact)) and	US - PGPUB	1
		(semiconductor wafer substrate)) and etch\$3	i	i
-	779	((((tapered near5 (electrode gate)) and	USPAT;	2003/10/30 15:
		(trench onen\$3 recess hole via contact)) and	US-PGPUB	1
		(semiconductor wafer substrate)) and etch\$3)		Ĭ.
		and mask	i	
	4471	phase near10 change near10 (device memory)	USPAT;	2003/10/30 15:4
i			US-PGPUB	1
!	7	(phase near10 change near10 (device memory))	USPAT;	2003/10/30 15:4
I	,	and (tapered near5 (electrode gate))	US-PGPUB	,,
1	4825	(gate electrode) near10 (etch\$3 pattern\$3)	USPAT;	2003/10/30 18:
İ	-023	near100 mask near100 (trench hole open\$3 via	US-PGPUB	1 2003/10/30 10:
		contact recess groove)	00 10100	!
_	1481		I HEDAT.	2002/10/20 10:1
1	1401	((gate electrode) near10 (etch\$3 pattern\$3)	USPAT;	2003/10/30 18:
į	1	near100 mask near100 (trench hole open\$3 via	US-PGPUB	1
į.	1473	contact recess groove)) and charge		1 0000 /10 /20 55
1	1471	(((gate electrode) near10 (etch\$3 pattern\$3)	USPAT;	2003/10/30 18:
		near100 mask near100 (trench hole open\$3 via	US-PGPUB	1
		contact recess groove)) and charge) and	ļ	
		(semiconductor wafer substrate)		i
- 1	2095	(gate electrode) near10 (etch\$3 pattern\$3)	EPO; JPO;	2003/10/30 18:
1		near100 mask near100 (trench hole open\$3 via	DERWENT;	-
1		contact recess groove)	IBM_TDB	1
i				1 2002 / 10 / 20 10 1
Ī		((gate electrode) near10 (etch\$3 pattern\$3)	EPO; JPO:	. 2003/10/30 18:3
İ		((gate electrode) near10 (etch\$3 pattern\$3) near100 mask near100 (trench hole open\$3 via	EPO; JPO; DERWENT;	2003/10/30 18:5